# Noninverting Buffer / CMOS Logic Level Shifter with TTL-Compatible Inputs

The MC74VHC1GT50 is a single gate noninverting buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The device input is compatible with TTL- type input thresholds and the output has a full 5 V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3.0 V CMOS logic to 5.0 V CMOS Logic or from 1.8 V CMOS logic to 3.0 V CMOS Logic while operating at the high-voltage power supply.

The MC74VHC1GT50 input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the MC74VHC1GT50 to be used to interface high voltage to low voltage circuits. The output structures also provide protection when  $V_{CC} = 0$  V. These input and output structures help prevent device destruction caused by supply voltage - input/output voltage mismatch, battery backup, hot insertion, etc.

- Designed for 1.65 V to 5.5 V<sub>CC</sub> Operation
- High Speed:  $t_{PD} = 3.5$  ns (Typ) at  $V_{CC} = 5$  V
- Low Power Dissipation:  $I_{CC} = 1 \ \mu A$  (Max) at  $T_A = 25^{\circ}C$
- TTL-Compatible Inputs:  $V_{IL} = 0.8 \text{ V}$ ;  $V_{IH} = 2.0 \text{ V}$ ,  $V_{CC} = 5 \text{ V}$
- CMOS-Compatible Outputs:  $V_{OH} > 0.8 V_{CC}$ ;  $V_{OL} < 0.1 V_{CC}$  @Load
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FETs = 104; Equivalent Gates = 26

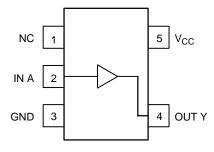


Figure 1. Pinout (Top View)

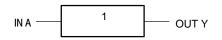
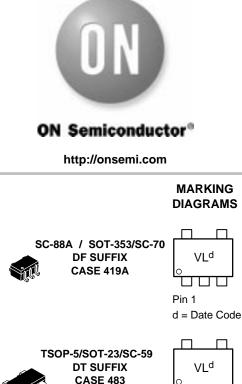


Figure 2. Logic Symbol



VL<sup>d</sup> Pin 1 d = Date Code

#### **PIN ASSIGNMENT**

1	NC
2	IN A
3	GND
4	OUT Y
5	V <sub>CC</sub>

#### **FUNCTION TABLE**

A Input	Y Output
L	L
Н	н

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

#### MAXIMUM RATINGS (Note 1)

Symbol	Charae	cteristics	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +7.0	V
V <sub>IN</sub>	DC Input Voltage		-0.5 to +7.0	V
V <sub>OUT</sub>	DC Output Voltage	V <sub>CC</sub> = 0 High or Low State	-0.5 to 7.0 -0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input Diode Current		-20	mA
I <sub>OK</sub>	Output Diode Current	V <sub>OUT</sub> < GND; V <sub>OUT</sub> > V <sub>CC</sub>	+20	mA
I <sub>OUT</sub>	DC Output Current, per Pin		+25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND		+50	mA
PD	Power dissipation in still air	SC-88A, TSOP-5	200	mW
$\theta_{JA}$	Thermal resistance	SC- 88A, TSOP- 5	333	°C/W
ΤL	Lead temperature, 1 mm from case for	. 10 s	260	°C
TJ	Junction temperature under bias		+150	°C
T <sub>stg</sub>	Storage temperature		-65 to +150	°C
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 N/A	V
I <sub>Latch- Up</sub>	Latch-Up Performance Abov	e V <sub>CC</sub> and Below GND at 125°C (Note 5)	±500	mA

1. Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

Tested to EIA/JESD22-A114-A Tested to EIA/JESD22-A115-A 2.

3.

4. Tested to JESD22-C101-A

5. Tested to EIA/JESD78

### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Characteristics	Min	Max	Unit	
V <sub>CC</sub>	DC Supply Voltage		1.65	5.5	V
V <sub>IN</sub>	DC Input Voltage		0.0	5.5	V
V <sub>OUT</sub>	DC Output Voltage	V <sub>CC</sub> = 0 High or Low State	0.0 0.0	5.5 V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range		-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time	$\begin{array}{l} {\sf V}_{\rm CC} = 3.3 \; {\sf V} \pm 0.3 \; {\sf V} \\ {\sf V}_{\rm CC} = 5.0 \; {\sf V} \pm 0.5 \; {\sf V} \end{array}$	0 0	100 20	ns/V

#### **Device Junction Temperature versus** Time to 0.1% Bond Failures

Junction		
Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

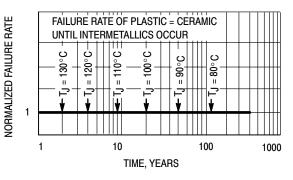


Figure 3. Failure Rate vs. Time Junction Temperature

## DC ELECTRICAL CHARACTERISTICS

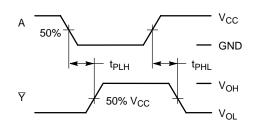
			V <sub>CC</sub>	Τ,	<b>∖ = 25</b> °	С	<b>T</b> <sub>A</sub> ≤	85°C	-55 ≤ T <sub>A</sub>	≤ 125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
VIH	Minimum		1.65 to 2.29	0.50 V <sub>CC</sub>			0.50 V <sub>CC</sub>		0.50 V <sub>CC</sub>		V
	High-Level Input Voltage		2.3 to 2.99	$0.45 V_{CC}$			$0.45 V_{CC}$		$0.45 V_{CC}$		
			3.0 4.5 5.5	1.4 2.0 2.0			1.4 2.0 2.0		1.4 2.0 2.0		
V <sub>IL</sub>	Maximum		1.65 to 2.29			0.10 V <sub>CC</sub>		0.10 V <sub>CC</sub>		0.10 V <sub>CC</sub>	V
	Low-Level Input Voltage		2.3 to 2.99			0.15 V <sub>CC</sub>		0.15 V <sub>CC</sub>		0.15 V <sub>CC</sub>	
			3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	
V <sub>OH</sub>	Minimum	$V_{IN} = V_{IH}$	1.65 to 2.99	V <sub>CC</sub> - 0.1			V <sub>CC</sub> - 0.1		V <sub>CC</sub> - 0.1		V
	High-Level Output Voltage	I <sub>OH</sub> = -50 μA	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		
		$V_{IN} = V_{IH}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V <sub>OL</sub>	Maximum	$V_{IN} = V_{IL}$	1.65 to 2.99		0.0	0.1		0.1		0.1	V
	Low-Level Output Voltage	$I_{OL} = 50 \ \mu A$	3.0 4.5		0.0	0.1 0.1		0.1 0.1		0.1 0.1	
		$V_{IN} = V_{IL}$ $I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I <sub>IN</sub>	Maximum Input Leakage Current	$V_{IN} = 5.5 \text{ V or GND}$	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			1.0		20		40	μΑ
I <sub>CCT</sub>	Quiescent Supply Current	Input: V <sub>IN</sub> = 3.4 V	5.5			1.35		1.50		1.65	mA
I <sub>OPD</sub>	Output Leakage Current	V <sub>OUT</sub> = 5.5 V	0.0			0.5		5.0		10	μΑ

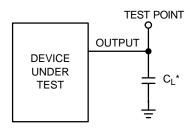
# AC ELECTRICAL CHARACTERISTICS $C_{\text{load}}$ = 50 pF, Input $t_{\text{r}}$ = $t_{\text{f}}$ = 3.0 ns

			1	Γ <sub>A</sub> = 25°	с	T <sub>A</sub> ≤	85°C		≤ T <sub>A</sub> ≤ 5°C	
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> ,	Maximum Propagation	$V_{CC}$ = 1.8 ± 0.15 V C <sub>L</sub> = 15 pF			16.6		18.0		22.0	ns
t <sub>PHL</sub>	Delay, Input A to Y	$V_{CC} = 2.5 \pm 0.2 \text{ V}  \begin{array}{c} C_L = 15 \text{ pF} \\ C_L = 50 \text{ pF} \end{array}$			13.3 19.5		14.5 22.0		17.5 25.5	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}  \begin{array}{c} C_L = 15 \text{ pF} \\ C_L = 50 \text{ pF} \end{array}$		4.5 6.3	10.0 13.5		11.0 15.0		13.0 17.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}  \begin{array}{c} C_L = 15 \text{ pF} \\ C_L = 50 \text{ pF} \end{array}$		3.5 4.3	6.7 7.7		7.5 8.5		8.5 9.5	
C <sub>IN</sub>	Maximum Input Capacitance			5	10		10		10	pF
					Туріс	cal @ 2	5°C, V <sub>CC</sub>	; = 5.0 \	/	

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
C <sub>PD</sub>	Power Dissipation Capacitance (Note 6)	12	pF
		ferrer the researching as successful researching with r	ام م م ا عب ب

6. C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.





\*Includes all probe and jig capacitance

## Figure 4. Switching Waveforms

## Figure 5. Test Circuit

### **DEVICE ORDERING INFORMATION**

			Device Nome					
Device Order Number	Circuit Indicator	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape & Reel Suffix	Package Type (Name/SOT#/ Common Name)	Tape and Reel Size
MC74VHC1GT50DFT1	MC	74	VHC1G	T50	DF	T1	SC-88A / SOT-353 / SC-70	178 mm (7") 3000 Unit
MC74VHC1GT50DFT2	MC	74	VHC1G	T50	DF	T2	SC-88A / SOT-353 / SC-70	178 mm (7") 3000 Unit
MC74VHC1GT50DTT1	MC	74	VHC1G	T50	DT	T1	TSOP-5 / SOT-23 / SC-59	178 mm (7") 3000 Unit

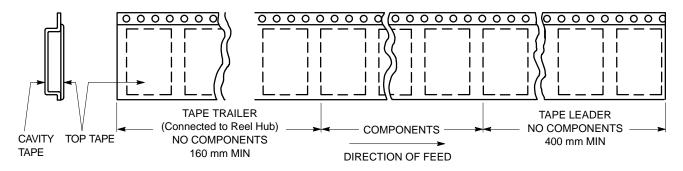
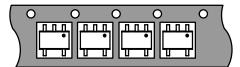
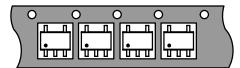


Figure 6. Tape Ends for Finished Goods

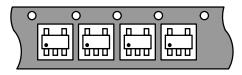


"T1" Pin One Toward Sprocket Hole (3k Reel)



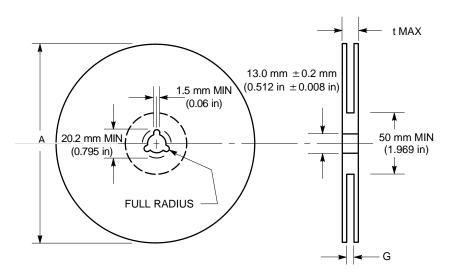
"T2" Pin One Opposing Sprocket Hole (3k Reel)

#### Figure 7. SC-88A/SOT-353/SC-70-5 DFT1 and DFT2 Reel Configuration/Orientation



"T1" Pin One Opposing Sprocket Hole (3k Reel)

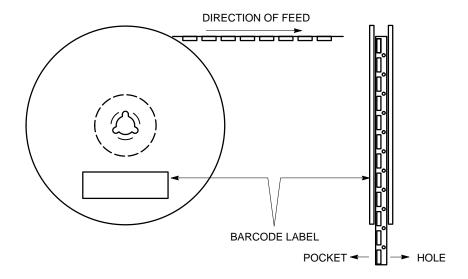
Figure 8. TSOP-5/SC59-5/SOT23-5 DTT1 Reel Configuration/Orientation

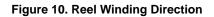




#### **REEL DIMENSIONS**

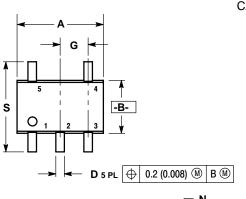
Tape Size	T and R Suffix	A Max	G	t Max
8 mm	T1, T2	178 mm (7 in)	8.4 mm, + 1.5 mm, -0.0 (0.33 in + 0.059 in, -0.00)	14.4 mm (0.56 in)

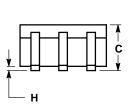


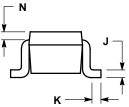


## PACKAGE DIMENSIONS

SC-88A / SOT-353 / SC-70 DF SUFFIX 5-LEAD PACKAGE CASE 419A-02 **ISSUE F** 

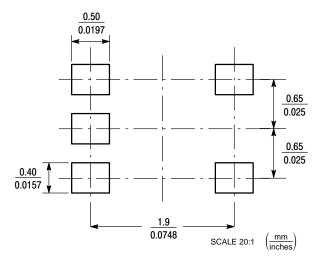






NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.

	INC	HES	MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65 BSC	
Н		0.004		0.10
J	0.004	0.010	0.10	0.25
κ	0.004	0.012	0.10	0.30
Ν	0.008 REF		0.20	REF
S	0.079	0.087	2.00	2.20



#### PACKAGE DIMENSIONS

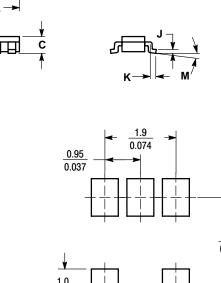
## TSOP-5 / SOT-23 / SC-59 DT SUFFIX 5-LEAD PACKAGE

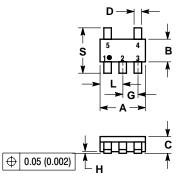
CASE 483-01 ISSUE B NOTES:

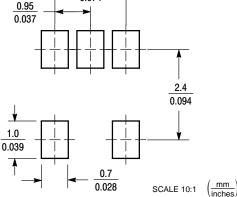
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2. CONTROLLING DIMENSION: MILLIMETER. 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	2.90	3.10	0.1142	0.1220	
В	1.30	1.70	0.0512	0.0669	
С	0.90	1.10	0.0354	0.0433	
D	0.25	0.50	0.0098	0.0197	
G	0.85	1.05	0.0335	0.0413	
Η	0.013	0.100	0.0005	0.0040	
L	0.10	0.26	0.0040	0.0102	
Κ	0.20	0.60	0.0079	0.0236	
L	1.25	1.55	0.0493	0.0610	
М	0 °	10°	0°	10 °	
s	2.50	3.00	0.0985	0.1181	







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